



P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
	0.150 at V _{GS} = - 4.5 V	1.06			
- 20	0.166 at V _{GS} = - 2.5V	1.0	6.0		
	0.214 at V _{GS} = - 1.8V	0.49			

FEATURES

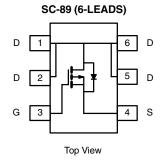
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

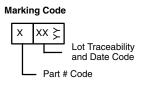


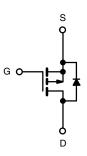
ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

· Load Switch for Portable Devices







Ordering Information: Si1067X-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unle	ess otherwise no	ted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 20	V	
Gate-Source Voltage		V _{GS}	± 8	v	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	,	- 1.06 ^{b, c}		
	T _A = 70 °C	I _D	- 0.85 ^{b, c}		
Pulsed Drain Current		I _{DM}	- 8	A	
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	- 0.2 ^{b, c}		
	T _A = 25 °C	P _D	0.236 ^{b, c}	w	
Maximum Power Dissipation ^a	T _A = 70 °C		0.151 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maningum Lungsting to Amphicata h	t ≤ 5 s	R _{thJA}	440	530	°C/W	
Maximum Junction-to-Ambient ^{a, b}	Steady State	' 'thJA	540	650		

Notes:

- a. Maximum under steady state conditions is 650 °C/W.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050 A		- 32.07		\//00	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	l _D = - 250 μA	3.02			mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.45		- 0.95	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
7 0	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 \text{ °C}$			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = \ge 5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 8			Α	
		V _{GS} = - 4.5 V, I _D = - 1.06 A		0.125	0.150		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 1.0 A		0.138	0.166	Ω	
		V _{GS} = - 1.8 V, I _D = - 0.49 A		0.165	0.214		
Forward Transconductance	9 _{fs}	V _{DS} = - 10 V, I _D = - 1.06 A		4.0		S	
Dynamic ^b						I.	
Input Capacitance	C _{iss}			375			
Output Capacitance	C _{oss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		82		pF	
Reverse Transfer Capacitance	C _{rss}			62			
Tatal Cata Observe	0	$V_{DS} = -10 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -1.06 \text{ A}$		6.5	9.3		
Total Gate Charge	Q_g			6.0	9.1	nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -1.06 \text{ A}$		0.76			
Gate-Drain Charge	Q _{gd}			2.23			
Gate Resistance	R _g	f = 1 MHz		8.8	13.2	Ω	
Turn-On Delay Time	t _{d(on)}			14	21		
Rise Time t _r		$V_{DD} = -10 \text{ V}, R_{L} = 19.74 \Omega$		22	33	1	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -0.76 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		48	72	ns	
Fall Time	t _f			17	25.5	1	
Drain-Source Body Diode Characteris	stics						
Pulse Diode Forward Current ^a	I _{SM}				8	Α	
Body Diode Voltage	V _{SD}	I _S = - 0.63 A		0.8	1.2	V	
Body Diode Reverse Recovery Time t _{rr}				12.8	19.2	nC	
Body Diode Reverse Recovery Charge	Q _{rr}	1 07 4 41/44 400 4/4-		4.5	6.8		
Reverse Recovery Fall Time	t _a	I _F = - 0.7 A, dI/dt = 100 A/μs		7.3		ns	
Reverse Recovery Rise Time	t _b			5.5			

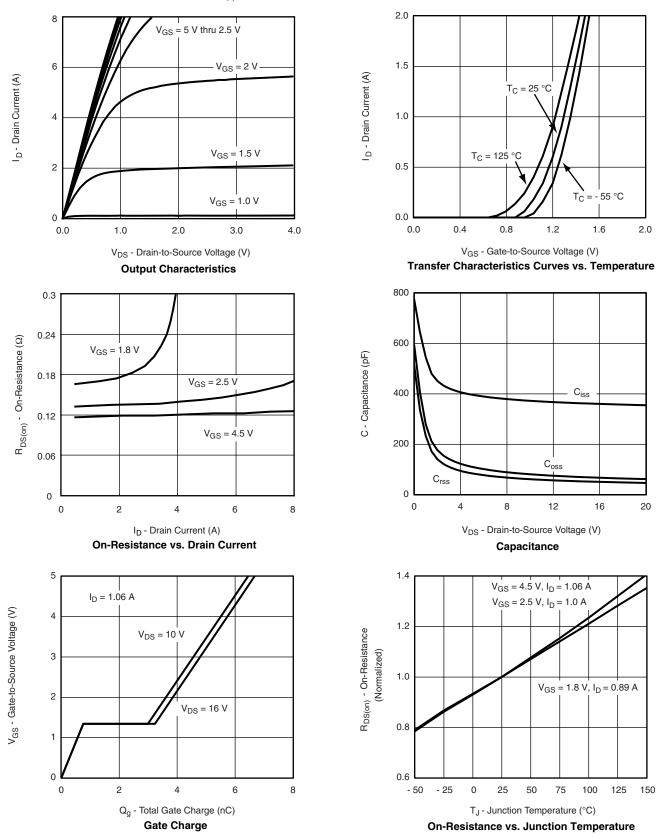
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



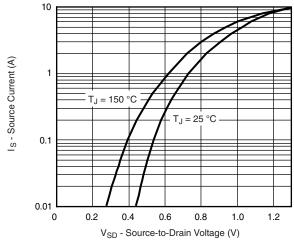
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



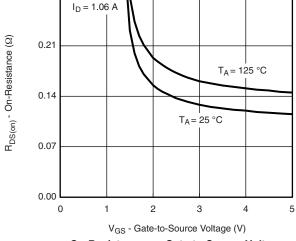
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TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

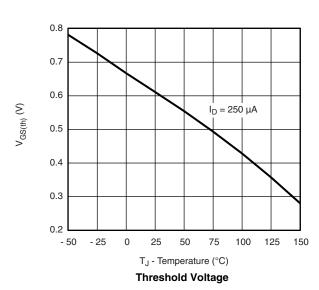


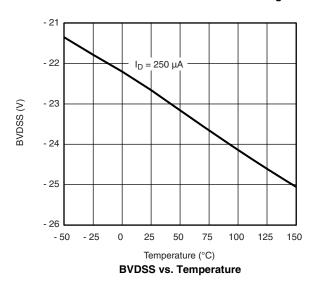
Source-Drain Diode Forward Voltage

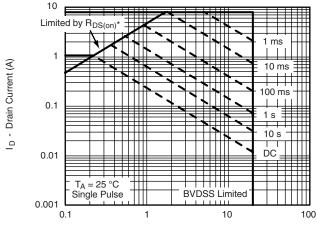


0.28

On-Resistance vs. Gate-to-Source Voltage







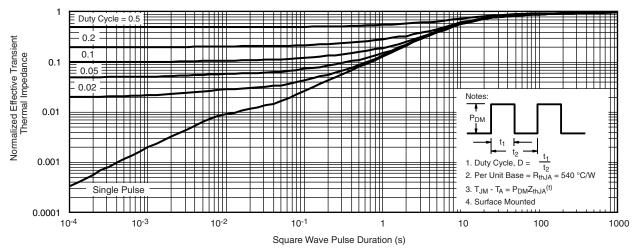
 $V_{DS} \text{ - Drain-to-Source Voltage (V)} \\ \text{* } V_{GS} > \text{ minimum } V_{GS} \text{ at which } R_{DS(on)} \text{ is specified} \\$

Safe Operating Area, Junction-to-Ambient





TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

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